

MOSFET – N-Channel, SUPERFET II, FRFET 600 V, 76 A, 41 mΩ

FCH041N60F-F085

Description

SUPERFET® II MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently SUPERFET II is very well suited for the Soft switching and Hard Switching topologies like High Voltage Full Bridge and Half Bridge DC-DC, Interleaved Boost PFC, Boost PFC for HEV-EV automotive. SUPERFET II FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.

Features

- Typical $R_{DS(on)}$ = 36 mΩ at $V_{GS} = 10$ V, $I_D = 38$ A
- Typical $Q_{g(tot)} = 267$ nC at $V_{GS} = 10$ V, $I_D = 38$ A
- Low Effective Output Capacitance (Typical $C_{oss(eff.)} = 720$ nF)
- 100% Avalanche Tested
- Qualified to AEC Q101 and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

Applications

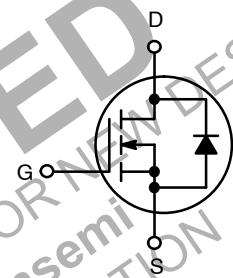
- Automotive On Board Charger
- Automotive DC/DC Converter for HEV



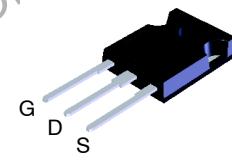
ON Semiconductor®

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V_{DSS}	$R_{DS(on) \text{ MAX}}$	$I_D \text{ MAX}$
600 V	41 mΩ	76 A

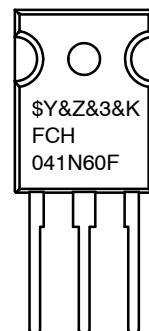


N-Channel MOSFET



TO-247
CASE 340CK

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot Code
FCH041N60F = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCH041N60F-F085

MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain to Source Voltage	600	V
V _{GS}	Gate to Source Voltage	±20	V
I _D	Drain Current – Continuous (V _{GS} = 10)	T _C = 25°C	76
	Pulsed Drain Current		See Fig. 4
E _{AS}	Single Pulsed Avalanche Rating (Note 1)	2025	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 2)	50	
P _D	Power Dissipation	595	W
	Derate Above 25°C	4.76	W/°C
T _J , T _{STG}	Operating and Storage Temperature (Note 3)	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Starting T_J = 25°C, L = 18 mH, I_{AS} = 15 A, V_{DD} = 100 V during inductor charging and V_{DD} = 0 V during time in avalanche.
2. I_{SD} ≤ 38 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 380 V, starting T_J = 25°C.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.21	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Quantity
FCH041N60F-F085	FCH041N60F	TO-247	-	-	30

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600	–	–	V
I_{DSS}	Drain to Source Leakage Current	$V_{\text{DS}} = 600 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 25^\circ\text{C}$	–	–	10	μA
		$V_{\text{DS}} = 600 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 150^\circ\text{C}$ (Note 4)	–	–	1	mA
I_{GSS}	Gate to Source Leakage Current	$V_{\text{GS}} = \pm 20 \text{ V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}, I_D = 250 \mu\text{A}$	3	4	5	V
$r_{\text{DS}(\text{on})}$	Static Drain to Source On Resistance	$V_{\text{GS}} = 10 \text{ V}, I_D = 38 \text{ A}, T_J = 25^\circ\text{C}$	–	36	41	$\text{m}\Omega$
		$V_{\text{GS}} = 10 \text{ V}, I_D = 38 \text{ A}, T_J = 150^\circ\text{C}$ (Note 4)	–	89	98	$\text{m}\Omega$

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{\text{DS}} = 100 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}$	–	10900	–	pF
C_{oss}	Output Capacitance		–	360	–	pF
C_{rss}	Reverse Transfer Capacitance		–	4.4	–	pF
$C_{\text{oss}(\text{eff.})}$	Effective Output Capacitance	$V_{\text{DS}} = 0 \text{ V to } 480 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	–	720	–	pF
R_g	Gate Resistance	$f = 1 \text{ MHz}$	–	0.7	–	Ω
$Q_{\text{g}(\text{TOT})}$	Total Gate Charge	$V_{\text{DD}} = 380 \text{ V}, I_D = 38 \text{ A}, V_{\text{GS}} = 10 \text{ V}$	–	267	347	nC
$Q_{\text{g}(\text{th})}$	Threshold Gate Charge		–	20	26	nC
Q_{gs}	Gate to Source Gate Charge		–	59	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	106	–	nC

SWITCHING CHARACTERISTICS

t_{on}	Turn-On Time	$V_{\text{DD}} = 380 \text{ V}, I_D = 38 \text{ A}, V_{\text{GS}} = 10 \text{ V}, R_G = 4.7 \Omega$	–	–	242	ns
$t_{\text{d}(\text{on})}$	Turn-On Delay Time		–	63	–	ns
t_r	Rise Time		–	48	–	ns
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time		–	214	–	ns
t_f	Fall Time		–	33	–	ns
t_{off}	Turn-Off Time		–	–	514	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source to Drain Diode Voltage	$I_{\text{SD}} = 38 \text{ A}, V_{\text{GS}} = 0 \text{ V}$	–	–	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 38 \text{ A}, dI_{\text{SD}}/dt = 100 \text{ A}/\mu\text{s}$ $V_{\text{DD}} = 480 \text{ V}$	–	219	–	ns
Q_{rr}	Reverse Recovery Charge		–	1.9	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 150^\circ\text{C}$. Product is not tested to this condition in production.

TYPICAL CHARACTERISTICS

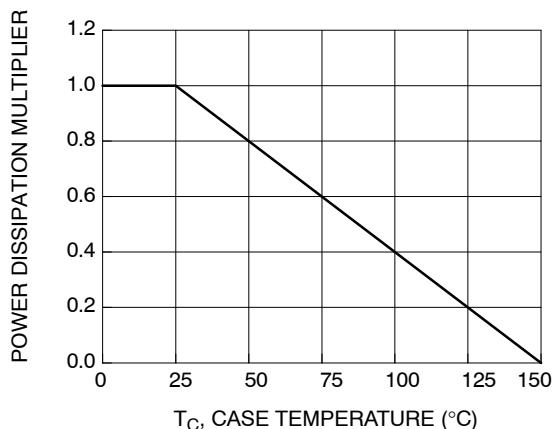


Figure 1. Normalized Power Dissipation vs. Case Temperature

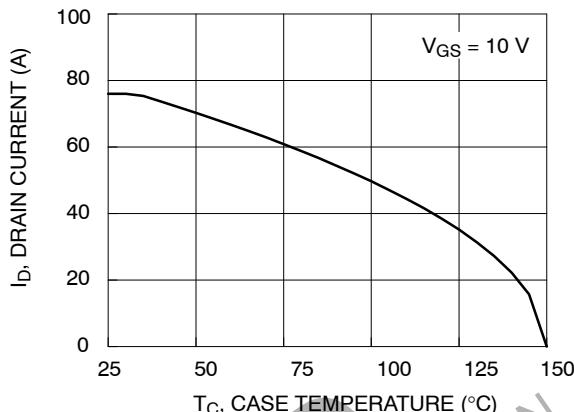


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

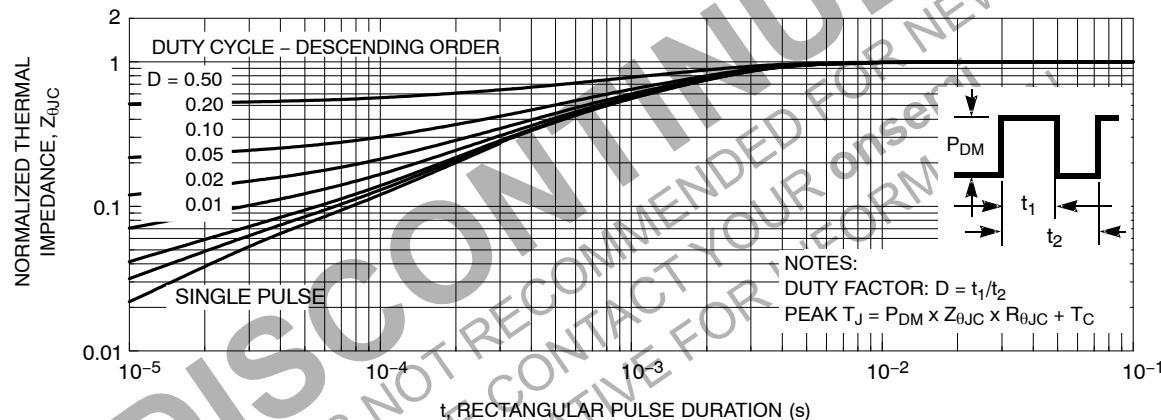


Figure 3. Normalized Maximum Transient Thermal Impedance

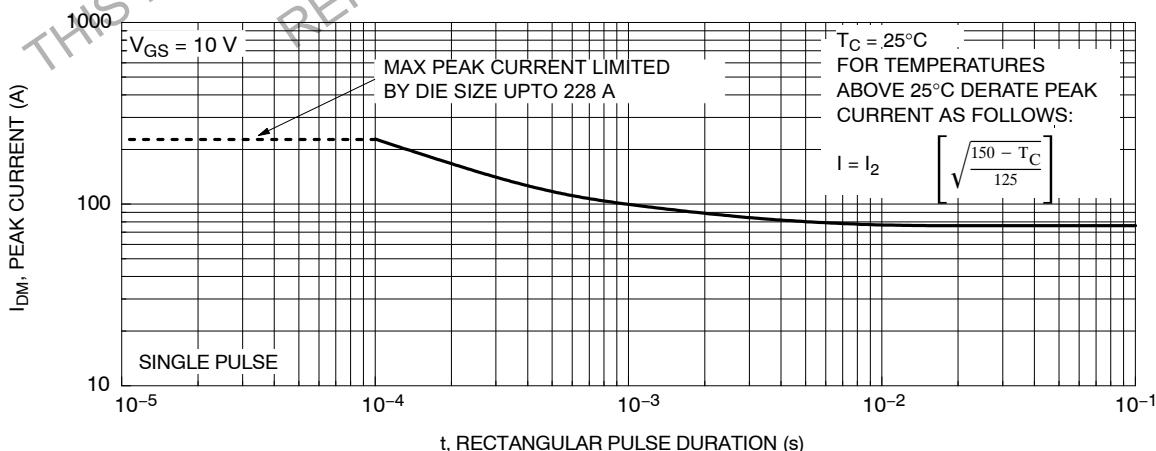


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

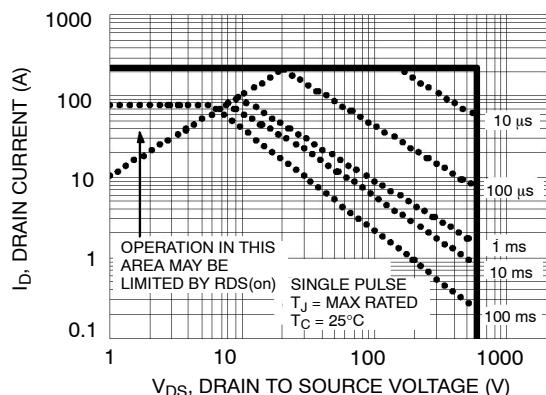


Figure 5. Forward Bias Safe Operating Area

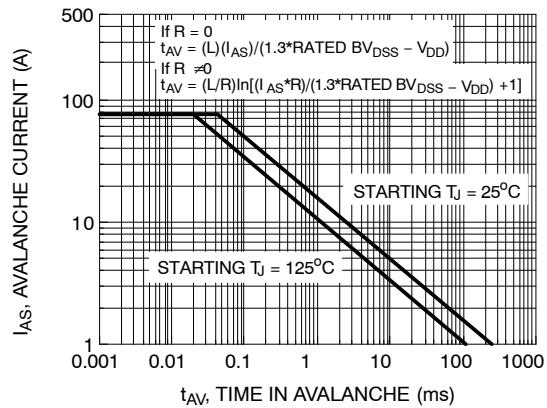


Figure 6. Unclamped Inductive Switching Capability

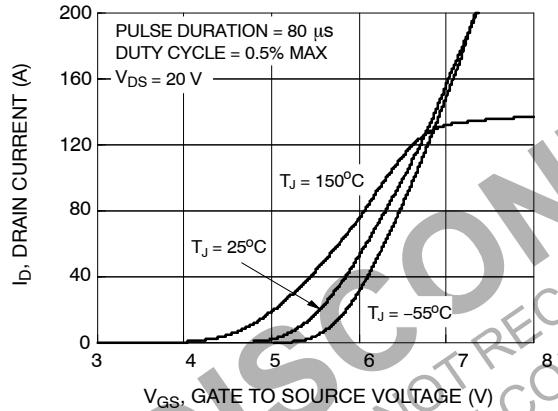


Figure 7. Transfer Characteristics

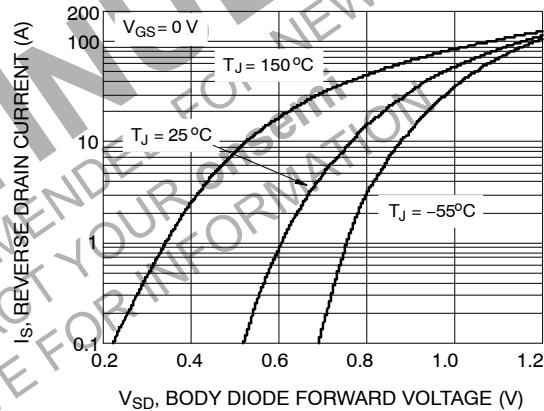


Figure 8. Forward Diode Characteristics

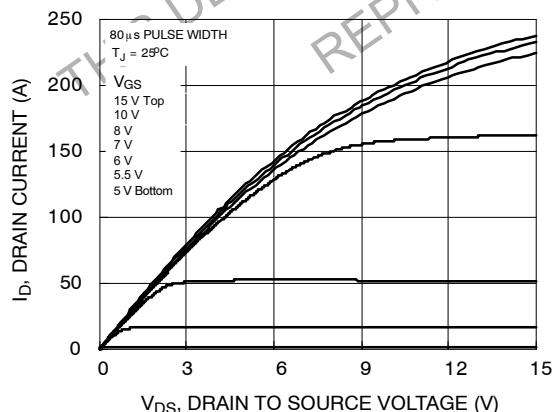


Figure 9. Saturation Characteristics

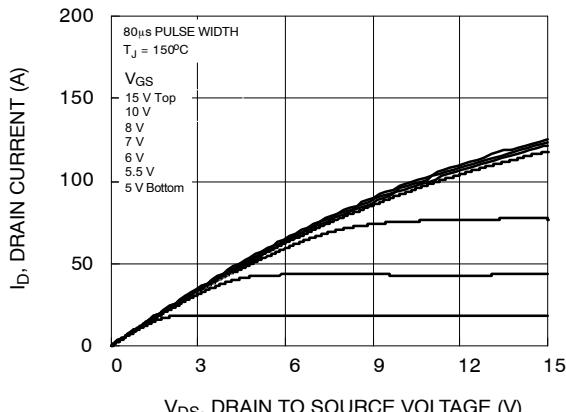


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

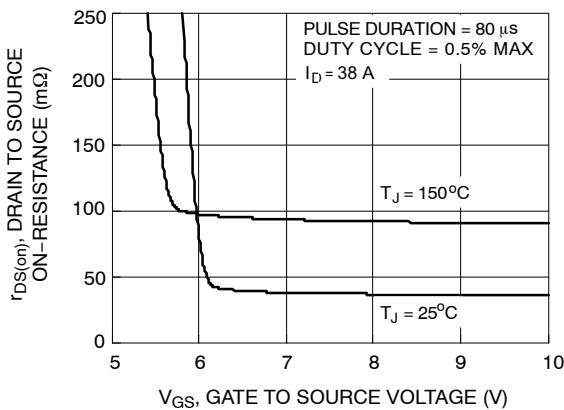


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

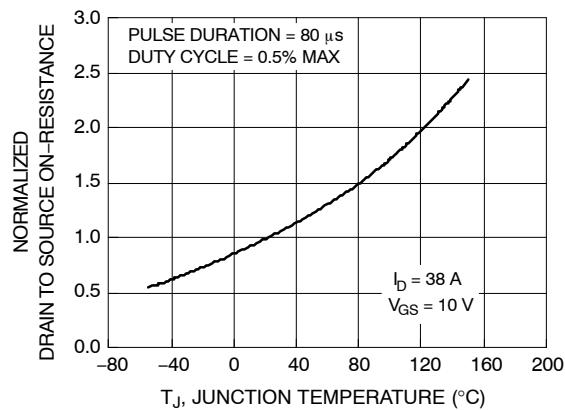


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

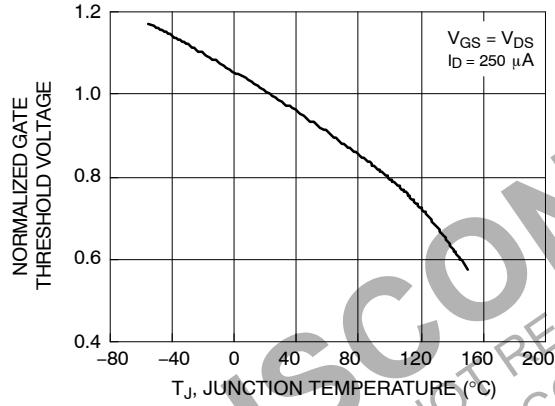


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

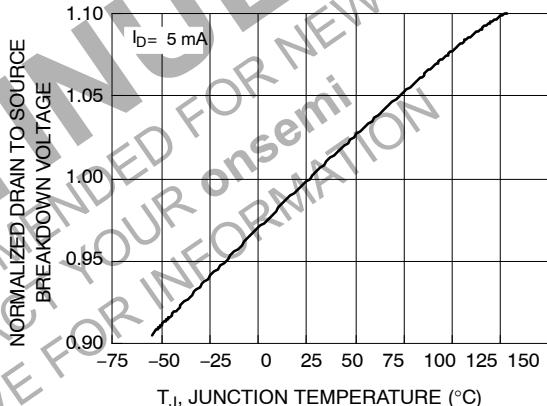


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

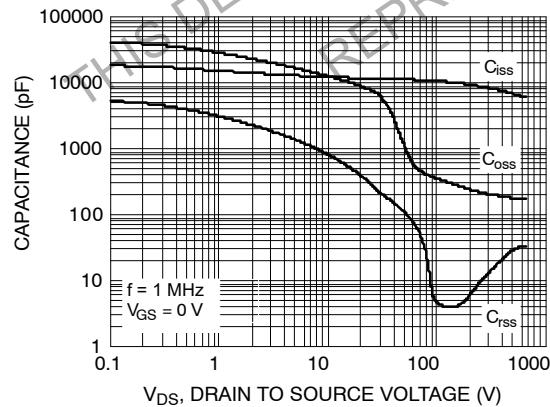


Figure 15. Capacitance vs. Drain to Source Voltage

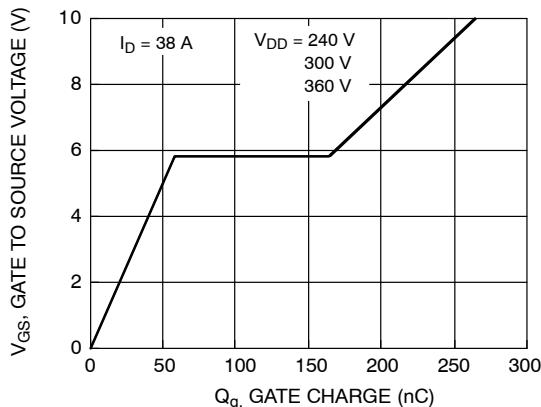


Figure 16. Gate Charge vs. Gate to Source Voltage

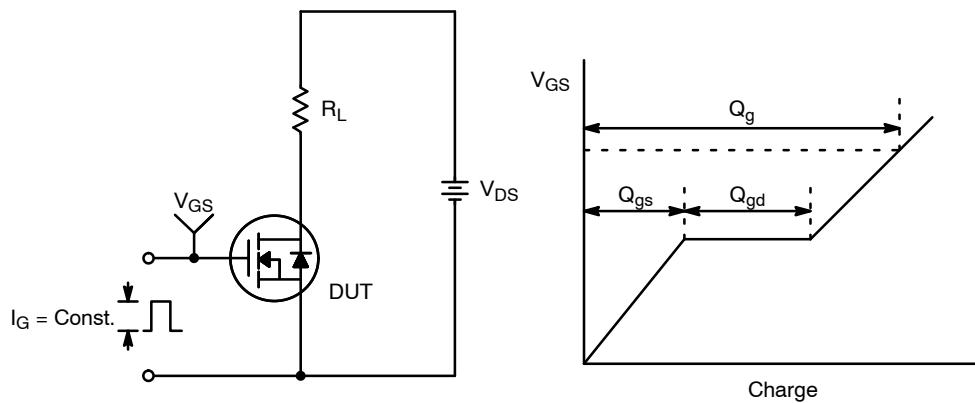


Figure 17. Gate Charge Test Circuit & Waveform

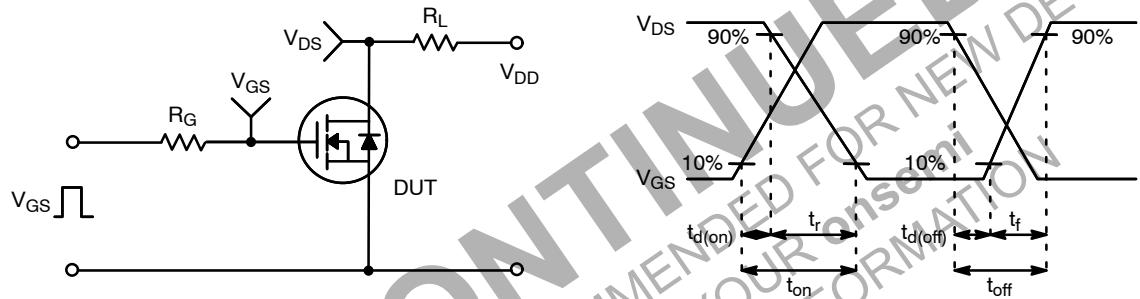


Figure 18. Resistive Switching Test Circuit & Waveforms

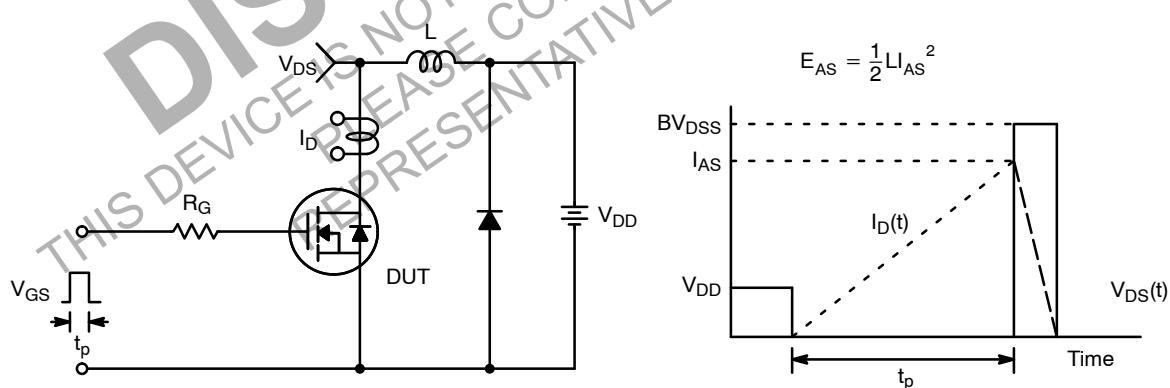


Figure 19. Unclamped Inductive Switching Test Circuit & Waveforms

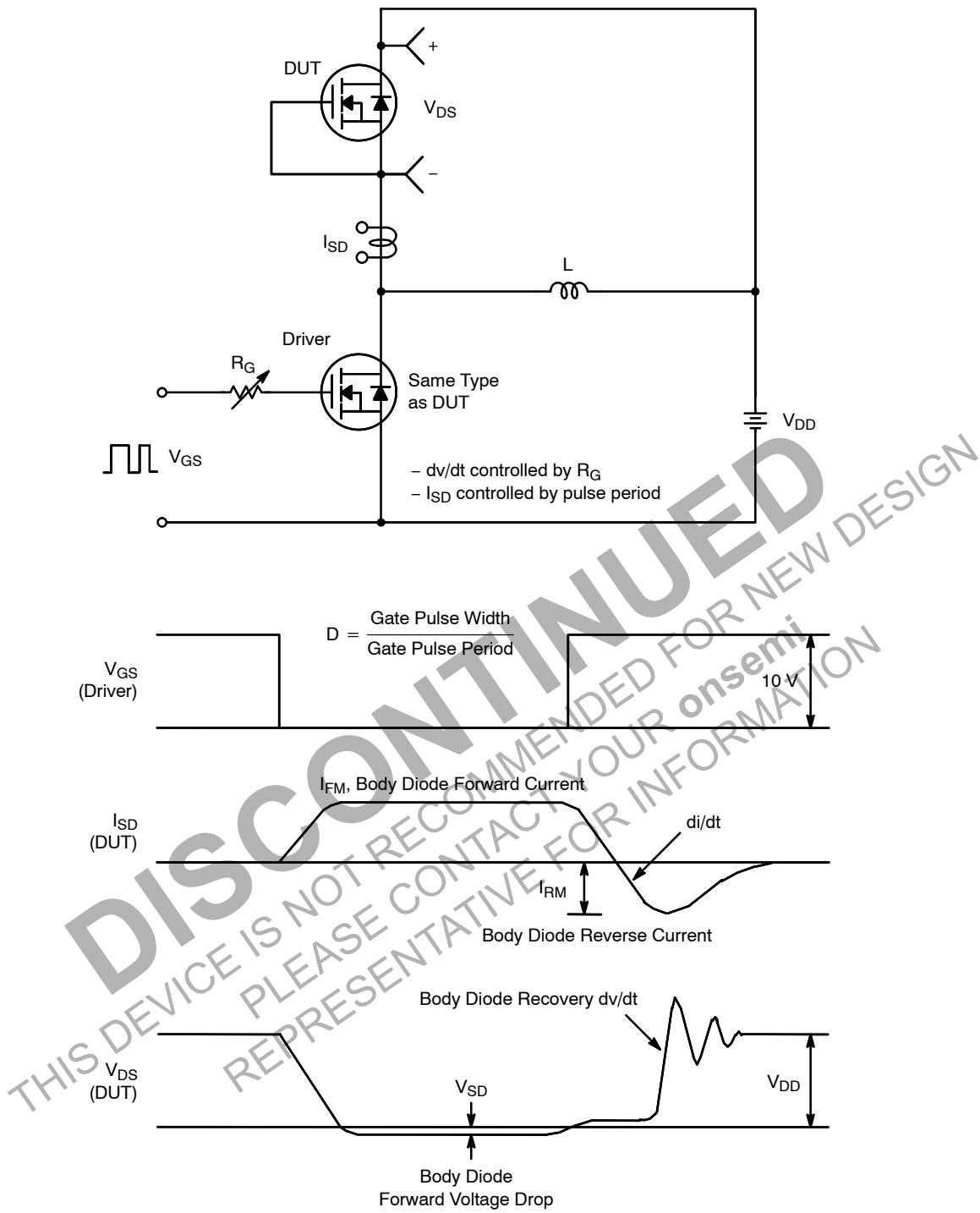
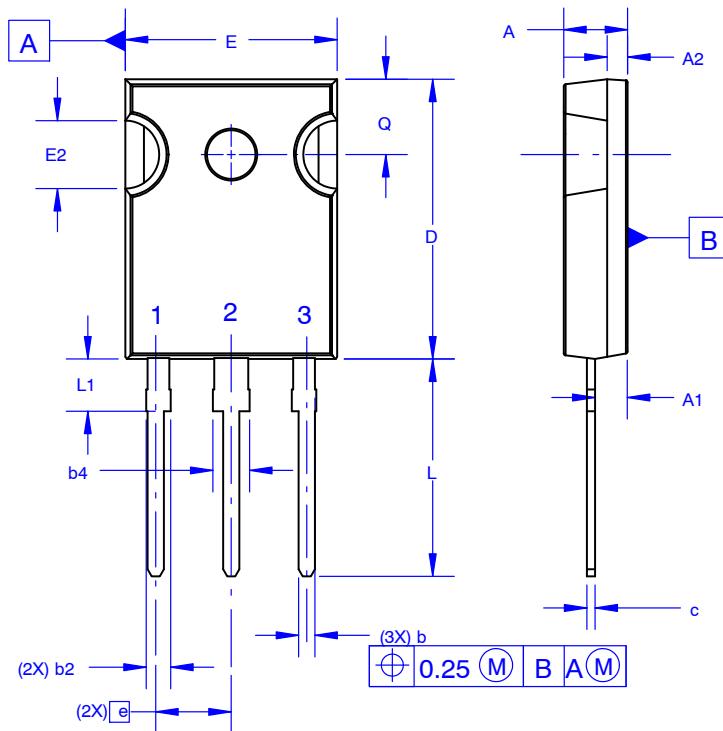


Figure 20. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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**TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A**



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot ":", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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DESCRIPTION:	TO-247-3LD SHORT LEAD	PAGE 1 OF 1

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